



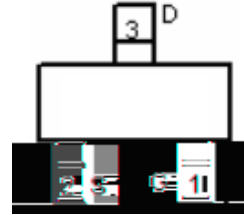
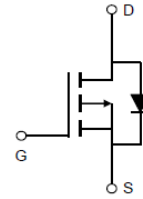
3

The ZM150N03T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

2

Advance high cell density Trench technology $R_{DS(ON)}$ to minimize conductive loss

Product Summary



nd Synchronous Rectifier

Part NO.	ZM150N03T
Marking	150N03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

$T_c = 25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25}$	8	A
	$I_{D@TC=75}$	6.1	A
	$I_{D@TC=100}$	5	A
Pulsed Drain Current	I_{DM}	16	A
Total Power Dissipation	P_D	10	W
Total Power Dissipation($T_A=25$)	$P_{D@TA=25}$	0.7	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy	E_{AS}	40	mJ



Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R _{thJC}	94.90	94.90		°C/W



Fig.1 Power Dissipation Derating Curve

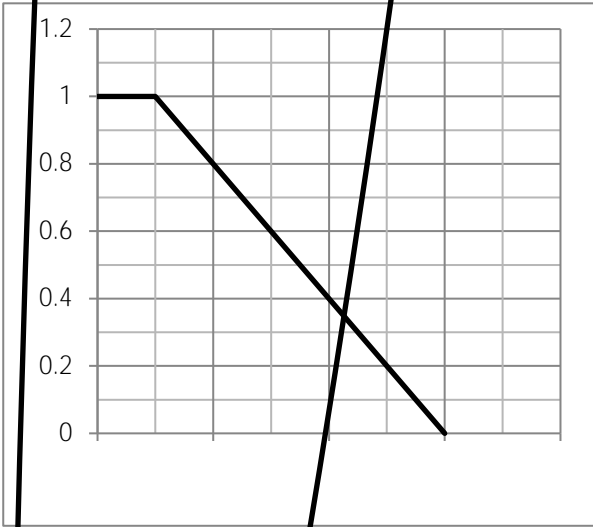


Fig.2 Typical output Characteristics

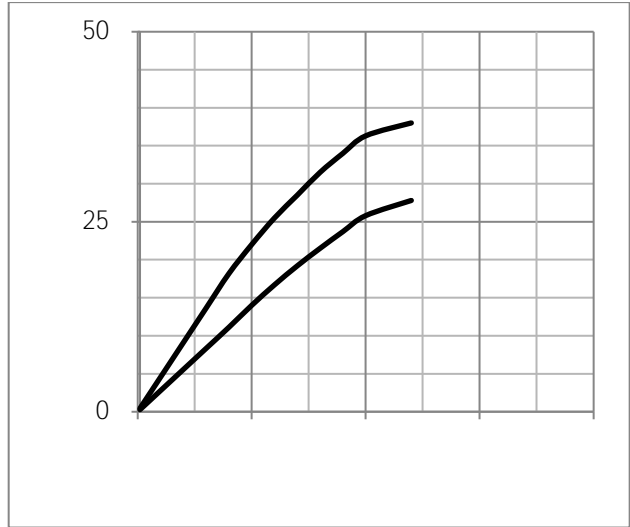


Fig.3 Threshold Voltage V.S Junction Temperature

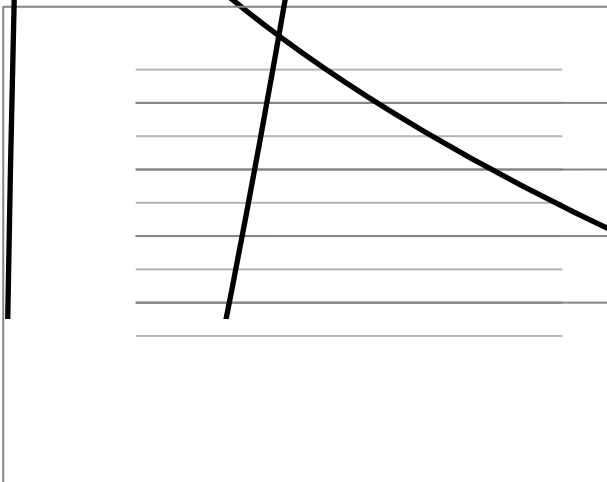
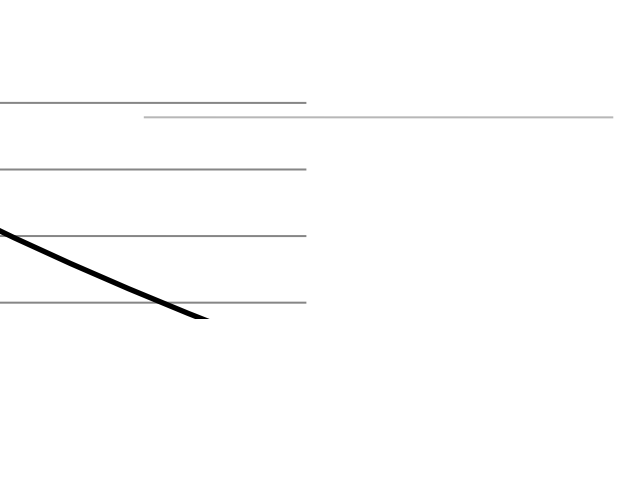


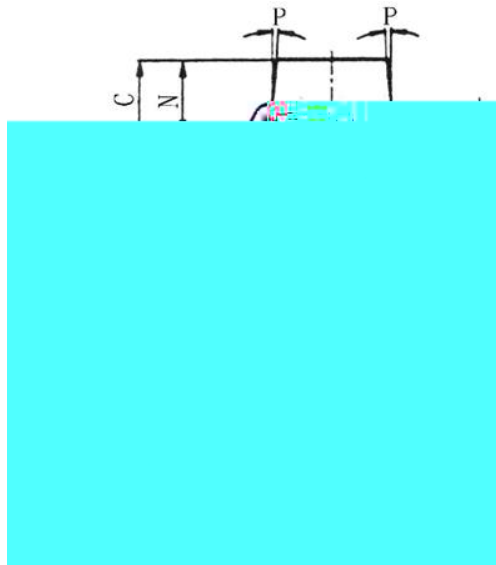
Fig.4 Resistance V.S Drain Current





(SOT23)

Unit mm



SYMBOL	min	nom	max
A	2.70	2.9	3.10
B	1.15	1.3	1.50
C			1.30
D	0.35	0.4	0.55
E	2.20	2.4	2.70
G	1.70	1.9	2.10
H	0.85	0.95	1.05
J	0.05	0.10	0.20
K	0.00		0.10
L	0.45	0.55	0.65



M	0.20		
N	0.90	1.00	1.20
P		7°	